

HV500F is high reliability resin molded type high voltage diode in small size package which is sealed a multilayered mesa type silicon chip by epoxy resin.

Features

- High speed switching
- Low VF
- High surge resistivity for CRT discharge
- High reliability design
- Ultra small package

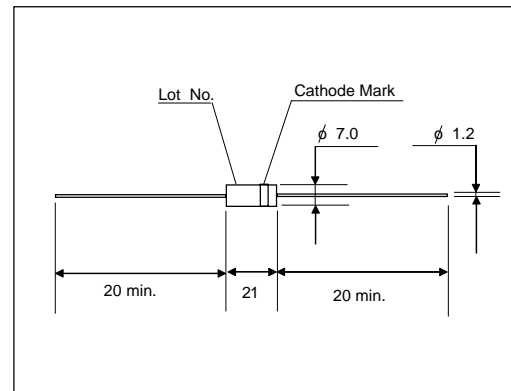
Applications

- X light Power supply
- Laser
- Voltage doubler circuit
- Microwave emission power

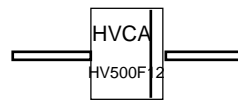
Maximum Ratings and Characteristics

- Absolute Maximum Ratings

Outline Drawings : mm



Cathode Mark

Type	Mark
HV500F12	

Items	Symbols	Condition	HV500F12	Units
Repetitive Peak Reverse Voltage	V_{RRM}		12	kV
Average Output Current	I_o	Ta=25°C, Resistive Load	450	mA
Surge Current	I_{FSM}		25	A _{peak}
Junction Temperature	T _J		155	°C
Allowable Operation Case Temperature	T _c		125	°C
Storage Temperature	T _{stg}		-40 to +155	°C

- Electrical Characteristics (Ta=25°C Unless otherwise specified)

Items	Symbols	Conditions	HV500F12	Units
Maximum Forward Voltage Drop	V_F	at 25°C, I _F =I _{F(AV)}	18	V
Maximum Reverse Current	IR1	at 25°C, V _R =V _{RRM}	5.0	μA
	IR2	at 100°C, V _R =V _{RRM}	50	μA
Maximum Reverse Recovery Time	T _{rr}	at 25°C	100	nS
Junction Capacitance	C _j	at 25°C, V _R =0V, f=1MHz	15	pF